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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	23
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	30-LSSOP (0.240", 6.10mm Width)
Supplier Device Package	30-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f102a7asp-x0

RL78/G12 1. OUTLINE

Table 1-1. List of Ordering Part Numbers

Pin Package Data flash Part Number count Application R5F1026AASP#V5, R5F10269ASP#V5, R5F10268ASP#V5, R5F10267ASP#V5, 20 20-pin plastic Mounted < R> pins LSSOP R5F10266ASP#V5 R5F1026AASP#X5, R5F10269ASP#X5, R5F10268ASP#X5, R5F10267ASP#X5, $(4.4 \times 6.5 \text{ mm},$ 0.65 mm pitch) R5F10266ASP#X5 D R5F1026ADSP#V5, R5F10269DSP#V5, R5F10268DSP#V5, R5F10267DSP#V5, R5F10266DSP#V5 R5F1026ADSP#X5, R5F10269DSP#X5, R5F10268DSP#X5, R5F10267DSP#X5, R5F10266DSP#X5 G R5F1026AGSP#V5, R5F10269GSP#V5, R5F10268GSP#V5, R5F10267GSP#V5, R5F10266GSP#V5 R5F1026AGSP#X5, R5F10269GSP#X5, R5F10268GSP#X5, R5F10267GSP#X5, B5F10266GSP#X5 R5F1036AASP#V5, R5F10369ASP#V5, R5F10368ASP#V5, R5F10367ASP#V5, Not mounted R5F10366ASP#V5 R5F1036AASP#X5, R5F10369ASP#X5, R5F10368ASP#X5, R5F10367ASP#X5, R5F10366ASP#X5 D R5F1036ADSP#V5, R5F10369DSP#V5, R5F10368DSP#V5, R5F10367DSP#V5, R5F10366DSP#V5 R5F1036ADSP#X5, R5F10369DSP#X5, R5F10368DSP#X5, R5F10367DSP#X5, R5F10366DSP#X5 24 24-pin plastic Mounted R5F1027AANA#U5, R5F10279ANA#U5, R5F10278ANA#U5, R5F10277ANA#U5 Α <R> **HWQFN** pins R5F1027AANA#W5, R5F10279ANA#W5, R5F10278ANA#W5, $(4 \times 4 \text{ mm}, 0.5)$ R5F10277ANA#W5 mm pitch) D R5F1027ADNA#U5, R5F10279DNA#U5, R5F10278DNA#U5, R5F10277DNA#U5 R5F1027ADNA#W5, R5F10279DNA#W5, R5F10278DNA#W5, R5F10277DNA#W5 G R5F1027AGNA#U5, R5F10279GNA#U5, R5F10278GNA#U5, R5F10277GNA#U5 R5F1027AGNA#W5, R5F10279GNA#W5, R5F10278GNA#W5, R5F10277GNA#W5 Not mounted Α R5F1037AANA#V5, R5F10379ANA#V5, R5F10378ANA#V5, R5F10377ANA#V5 R5F1037AANA#X5, R5F10379ANA#X5, R5F10378ANA#X5, R5F10377ANA#X5 D R5F1037ADNA#V5, R5F10379DNA#V5, R5F10378DNA#V5, R5F10377DNA#V5 R5F1037ADNA#X5, R5F10379DNA#X5, R5F10378DNA#X5, R5F10377DNA#X5 R5F102AAASP#V0, R5F102A9ASP#V0, R5F102A8ASP#V0, R5F102A7ASP#V0 30 30-pin plastic Mounted Α LSSOP R5F102AAASP#X0, R5F102A9ASP#X0, R5F102A8ASP#X0, R5F102A7ASP#X0 pins (7.62 mm D R5F102AADSP#V0, R5F102A9DSP#V0, R5F102A8DSP#V0, R5F102A7DSP#V0 (300), 0.65 mm R5F102AADSP#X0, R5F102A9DSP#X0, R5F102A8DSP#X0, R5F102A7DSP#X0 pitch) G R5F102AAGSP#V0. R5F102A9GSP#V0. R5F102A8GSP#V0. R5F102A7GSP#V0 R5F102AAGSP#X0, R5F102A9GSP#X0, R5F102A8GSP#X0, R5F102A7GSP#X0 R5F103AAASP#V0, R5F103A9ASP#V0, R5F103A8ASP#V0, R5F103A7ASP#V0 Not mounted Α R5F103AAASP#X0, R5F103A9ASP#X0, R5F103A8ASP#X0, R5F103A7ASP#X0 R5F103AADSP#V0. R5F103A9DSP#V0. R5F103A8DSP#V0. R5F103A7DSP#V0 D R5F103AADSP#X0, R5F103A9DSP#X0, R5F103A8DSP#X0, R5F103A7DSP#X0

Note For fields of application, see Figure 1-1 Part Number, Memory Size, and Package of RL78/G12.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



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1.3 Differences between the R5F102 Products and the R5F103 Products

The following are differences between the R5F102 products and the R5F103 products.

- O Whether the data flash memory is mounted or not
- O High-speed on-chip oscillator oscillation frequency accuracy
- O Number of channels in serial interface
- O Whether the DMA function is mounted or not
- O Whether a part of the safety functions are mounted or not

1.3.1 Data Flash

The data flash memory of 2 KB is mounted on the R5F102 products, but not on the R5F103 products.

Product	Data Flash
R5F102 products	2KB
R5F1026A, R5F1027A, R5F102AA,	
R5F10269, R5F10279, R5F102A9,	
R5F10268, R5F10278, R5F102A8,	
R5F10267, R5F10277, R5F102A7,	
R5F10266 Note	
R5F103 products	Not mounted
R5F1036A, R5F1037A, R5F103AA,	
R5F10369, R5F10379, R5F103A9,	
R5F10368, R5F10378 R5F103A8,	
R5F10367, R5F10377, R5F103A7,	
R5F10366	

Note The RAM in the R5F10266 has capacity as small as 256 bytes. Depending on the customer's program specification, the stack area to execute the data flash library may not be kept and data may not be written to or erased from the data flash memory.

Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

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(2/2)

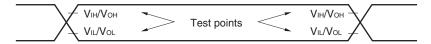
Item	20.	-pin	24.	-pin	30-	nin (2/2			
nom		R5F1026x	R5F1036x	R5F1027x	R5F1037x	R5F102Ax	R5F103Ax		
Clock output/buzzer ou	tout	1101 1020		1	1101 1007	HSI-102AX			
2.35K 04Kpdb04Z20I 04	-12-01	2.44 kHz to 10		al hardware cloc	ck: f _{MAIN} = 20 MH	l	-		
8/10-bit resolution A/D	converter		11 ch	8 cha	nnels				
Serial interface		[R5F1026x (20	[R5F1026x (20-pin), R5F1027x (24-pin)]						
		CSI: 2 chann	• CSI: 2 channels/Simplified I ² C: 2 channels/UART: 1 channel						
		[R5F102Ax (30	[R5F102Ax (30-pin)]						
		CSI: 1 chann	• CSI: 1 channel/Simplified I ² C: 1 channel/UART: 1 channel						
		CSI: 1 chann	nel/Simplified I ² C	: 1 channel/UAF	RT: 1 channel				
		CSI: 1 chann	nel/Simplified I ² C	: 1 channel/UAF	RT: 1 channel				
l		[R5F1036x (20)-pin), R5F1037	k (24-pin)]					
		CSI: 1 chann	nel/Simplified I ² C	: 0 channel/UAF	RT: 1 channel				
		[R5F103Ax (30-pin)]							
		CSI: 1 channel/Simplified I ² C: 0 channel/UART: 1 channel							
	I ² C bus			annel					
Multiplier and divider/multiply-		• 16 bits × 16 l	• 16 bits × 16 bits = 32 bits (unsigned or signed)						
accumulator		• 32 bits × 32 bits = 32 bits (unsigned)							
		• 16 bits × 16 bits + 32 bits = 32 bits (unsigned or signed)							
DMA controller	_	2 channels	_	2 channels	_	2 channels	_		
Vectored interrupt	Internal	18	16	18	16	26	19		
sources	External			5		6	6		
Key interrupt		(6	1	0	_	_		
Reset		Reset by RE							
			t by watchdog tir						
			t by power-on-re t by voltage dete						
			-		Note				
			Internal reset by illegal instruction execution Note Internal reset by RAM parity error						
		• Internal rese	t by illegal-mem	ory access					
Power-on-reset circuit			Power-on-reset: 1.51 V (TYP) Power-down-reset: 1.50 V (TYP)						
Voltage detector		Rising edge	• Rising edge : 1.88 to 4.06 V (12 stages)						
		• Falling edge : 1.84 to 3.98 V (12 stages)							
On-chip debug function	1	Provided							
Power supply voltage		V _{DD} = 1.8 to 5.5 V							
Operating ambient tem	perature	$T_A = -40 \text{ to } +88$ (G: Industrial a	•	er applications,	D: Industrial app	olications), TA = -	40 to +105°C		

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2.5 Peripheral Functions Characteristics

AC Timing Test Point



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

	(1A = 10 to 100 c) 110 t = 135 = 010 t) 135 = 0 t)									
Parameter	Symbol	Conditions		h-speed Mode	,	/-speed Mode	Unit			
			MIN.	MAX.	MIN.	MAX.				
Transfer rate				fмск/6		fмск/6	bps			
Note 1		Theoretical value of the maximum transfer rate $f_{\text{CLK}} = f_{\text{MCK}}^{\text{Note2}}$		4.0		1.3	Mbps			

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

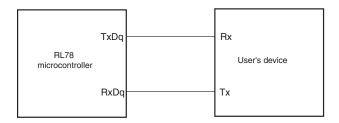
HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

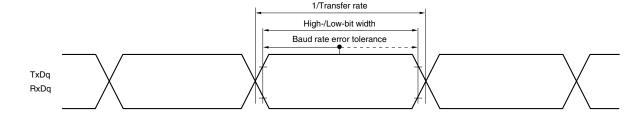
LS (low-speed main) mode: $8 \text{ MHz} (1.8 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V})$

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)

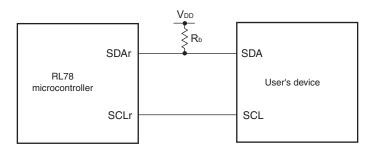


Remarks 1. q: UART number (q = 0 to 2), g: PIM, POM number (g = 0, 1)

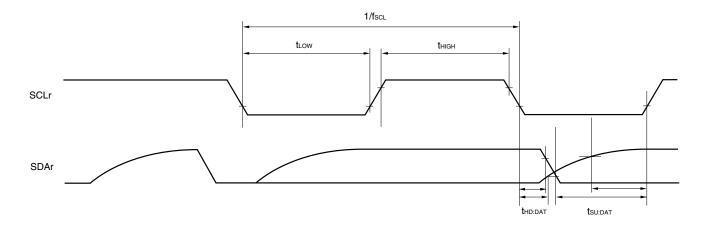
2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

Simplified I²C mode connection diagram (during communication at same potential)

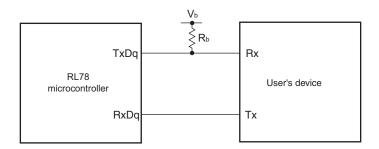


Simplified I²C mode serial transfer timing (during communication at same potential)

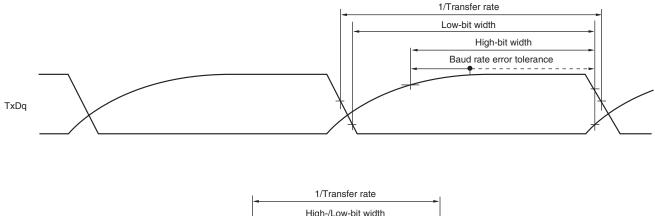


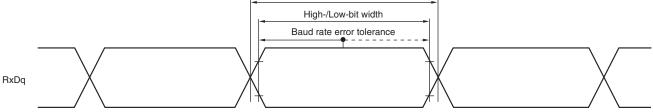
- Remarks 1. Rb $[\Omega]$:Communication line (SDAr) pull-up resistance Cb [F]: Communication line (SCLr, SDAr) load capacitance
 - 2. r: IIC number (r = 00, 01, 11, 20), h: = POM number (h = 0, 1, 4, 5)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (0, 1, 3))
 - 4. Simplified I²C mode is supported only by the R5F102 products.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remarks 1.** R_b[Ω]: Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
 - m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))
 - **4.** UART0 of the 20- and 24-pin products supports communication at different potential only when the peripheral I/O redirection function is not used.

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCK00... internal clock output, corresponding CSI00 only)

(Ta = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	ol Conditions			h-speed Mode	-	/-speed Mode	Unit
				MIN.	MAX.	MIN.	MAX.	
SCK00 cycle time	tkcy1	tkcy1 ≥ 2/fCLK	$\begin{aligned} &4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 20 \text{ pF}, \text{ R}_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$	200		1150		ns
			$\begin{split} 2.7 & \ V \le V_{DD} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b = 20 & \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	300		1150		ns
SCK00 high-level width	tкн1	$4.0 \text{ V} \le \text{V}_{DD} \le 5.$ $C_b = 20 \text{ pF}, R_b =$	5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 k Ω	tксу1/2 — 50		tксү1/2— 50		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	$0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$ = $2.7 \text{ k}\Omega$	tксу1/2 — 120		tксу1/2 – 120		ns
SCK00 low-level width	t _{KL1}	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$ $C_{\text{b}} = 20 \text{ pF, R}_{\text{b}} =$	5 V, 2.7 V \leq Vb \leq 4.0 V, = 1.4 k Ω	tксу1/2 — 7		tксү1/2 – 50		ns
		$2.7~V \leq V_{DD} < 4.$ $C_b = 20~pF,~R_b =$	tксу1/2 — 10		tксү1/2 – 50		ns	
SI00 setup time (to SCK00↑) Note 1		$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.$ $C_b = 20 \text{ pF}, \text{ Rb} =$	58		479		ns	
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	121		479		ns	
SI00 hold time (from SCK00↑) Note 1	tksi1	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.$ $C_b = 20 \text{ pF, R}_b =$	10		10		ns	
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	10		10		ns	
Delay time from SCK00↓ to SO00 output Note 1	tkso1	$4.0 \text{ V} \le V_{DD} \le 5.$ $C_b = 20 \text{ pF}, R_b =$	5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ		60		60	ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq Vb \leq 2.7 V, = 2.7 k Ω		130		130	ns
SI00 setup time (to SCK00↓) Note 2	tsıĸı	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.$ $C_b = 20 \text{ pF, R}_b =$	5 V, 2.7 V \leq Vb \leq 4.0 V, $= 1.4 \ k\Omega$	23		110		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq Vb \leq 2.7 V, = 2.7 k Ω	33		110		ns
SI00 hold time (from SCK00↓) Note 2	tksi1	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.$ $C_b = 20 \text{ pF}, \text{ R}_b =$	$5~V,~2.7~V \leq V_b \leq 4.0~V,$ = 1.4 k Ω	10		10		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq Vb \leq 2.7 V, = 2.7 k Ω	10		10		ns
Delay time from SCK00↑ to SO00 output Note 2	t _{KSO1}	$4.0~V \leq V_{DD} \leq 5.$ $C_b = 20~pF,~R_b =$	5 V, 2.7 V \leq Vb \leq 4.0 V, = 1.4 k Ω		10		10	ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 k Ω		10		10	ns

(Notes, Caution, and Remarks are listed on the next page.)



- Notes 1. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1
 - **2.** When DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
- Caution Select the TTL input buffer for the SI00 pin and the N-ch open drain output (VDD tolerance) mode for the SO00 pin and SCK00 pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1).

 For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** Rb [Ω]:Communication line (SCK00, SO00) pull-up resistance, Cb [F]: Communication line (SCK00, SO00) load capacitance, Vb [V]: Communication line voltage
 - fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS00 bit of serial mode register 00 (SMR00).)

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Co	onditions	HS (high-spe		LS (low-spe	•	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	$4.0~V \leq V_{DD} \leq 5.5~V,$	20 MHz < fмcк ≤ 24 MHz	12/fмск		-		ns
		$2.7~V \leq V_b \leq 4.0~V$	8 MHz < fмcк ≤ 20 MHz	10/fмск		=		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/fмск		ns
			fмcк ≤ 4 MHz	6/fмск		10/fмск		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$	20 MHz < fмcк ≤ 24 MHz	16/fмск		_		ns
		$2.3~V \leq V_b \leq 2.7~V$	16 MHz < fмcк ≤ 20 MHz	14/fмск		=		ns
			8 MHz < fмск ≤ 16 MHz	12/fмск		_		ns
			4 MHz < fмск ≤ 8 MHz	8/fмск		16/fмск		ns
			fмcк ≤ 4 MHz	6/fмск		10/fмск		ns
		$1.8 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$	20 MHz < fмcк ≤ 24 MHz	36/fмск		_		ns
		$1.6~V \leq V_b \leq 2.0~V$	16 MHz < fмcк ≤ 20 MHz	32/fмск		=		ns
		Note 2	8 MHz < fмск ≤ 16 MHz	26/fмск		_		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		16/fмск		ns
			fмcк ≤ 4 MHz	10/fмск		10/fмск		ns
SCKp high-/low-level	t _{KH2} ,	$4.0~V \leq V_{DD} \leq 5.5~V,$	tkcy2/2 - 12		tkcy2/2 - 50		ns	
width	t _{KL2}	$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$	$2.3~V \leq V_b \leq 2.7~V$	tkcy2/2 - 18		tkcy2/2 - 50		ns
		$1.8 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$	$1.6~V \leq V_b \leq 2.0~V^{\text{Note 2}}$	tkcy2/2 - 50		tkcy2/2 - 50		ns
SIp setup time	tsik2	$4.0~V \leq V_{DD} \leq 5.5~V,$	$2.7~V \leq V_{DD} \leq 4.0~V$	1/fmck + 20		1/fмск + 30		ns
(to SCKp↑) Note 3		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$	$2.3~V \leq V_b \leq 2.7~V$	1/fmck + 20		1/fмск + 30		ns
		$1.8 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$	$1.6~V \leq V_{DD} \leq 2.0~V^{\text{ Note 2}}$	1/fmck + 30		1/fмск + 30		ns
SIp hold time (from SCKp [↑]) Note 4	tksi2			1/fмск + 31		1/fмск + 31		ns
Delay time from	tkso2	$4.0~V \leq V_{DD} \leq 5.5~V,$	$2.7 \text{ V} \le V_b \le 4.0 \text{ V},$		2/fмск +		2/fмск +	ns
SCKp↓ to SOp		C _b = 30 pF, R _b = 1.4	$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$		120		573	
output Note 5		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$	$2.3 \text{ V} \le V_b \le 2.7 \text{ V},$		2/fмск +		2/fмск +	ns
		C _b = 30 pF, R _b = 2.7	kΩ		214		573	
		$1.8 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$	$1.6 \text{ V} \le V_b \le 2.0 \text{ V}^{\text{Note 2}},$		2/fмск +		2/fмск +	ns
	1	C _b = 30 pF, R _b = 5.5	kΩ		573		573	

Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

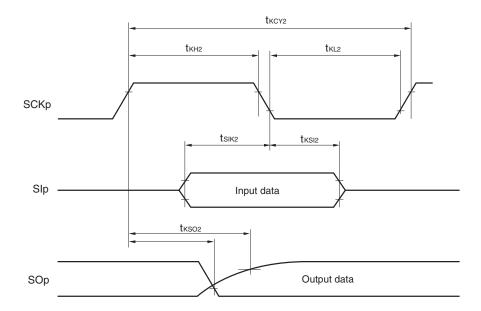
- 2. Use it with $V_{DD} \ge V_b$.
- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **5.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp \uparrow " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Cautions 1. Select the TTL input buffer for the SIp and SCKp pins and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1).

For VIH and VIL, see the DC characteristics with TTL input buffer selected.

2. CSI01 and CSI11 cannot communicate at different potential.

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

2.9 Dedicated Flash Memory Programmer Communication (UART)

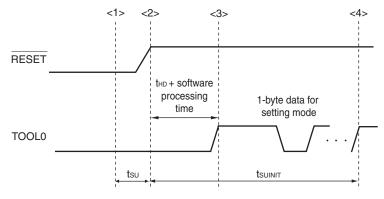
 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	ol Conditions		TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

2.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

TA = -40 to +65 C, 1.6 V \(\text{VDD} \(\text{DD} \(\text{S} \) \(\text{VS} \) \(\text{VS} \)									
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit			
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset are released before external reset release			100	ms			
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset are released before external reset release	10			μS			
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tho	POR and LVD reset are released before external reset release	1			ms			



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

 t_{SU} : Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(3/4)

Parameter	Symbol	Condition	ıs	MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	Normal input buffer		0.8V _{DD}		V _{DD}	٧
		20-, 24-pin products: P00 to P0 P40 to P42					
		30-pin products: P00, P01, P1 P40, P50, P51, P120, P147	0 to P17, P30, P31,				
	V _{IH2}	TTL input buffer	$4.0~V \leq V_{DD} \leq 5.5~V$	2.2		V _{DD}	V
		20-, 24-pin products: P10, P11	$3.3~V \leq V_{DD} < 4.0~V$	2.0		V _{DD}	٧
		30-pin products: P01, P10, P11, P13 to P17	$2.4~\textrm{V} \leq \textrm{V}_\textrm{DD} < 3.3~\textrm{V}$	1.5		V _{DD}	V
	V _{IH3}	Normal input buffer P20 to P23	·			V _{DD}	V
	V _{IH4}	P60, P61	0.7V _{DD}		6.0	٧	
	V _{IH5}	P121, P122, P125 ^{Note 1} , P137, I	0.8V _{DD}		V _{DD}	٧	
Input voltage, low	V _{IL1}	Normal input buffer		0		0.2V _{DD}	٧
		20-, 24-pin products: P00 to P0 P40 to P42					
		30-pin products: P00, P01, P10 P40, P50, P51, P120, P147					
	V _{IL2}	TTL input buffer	$4.0~V \leq V_{DD} \leq 5.5~V$	0		0.8	٧
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}$	0		0.5	٧
		30-pin products: P01, P10, P11, P13 to P17	2.4 V ≤ V _{DD} < 3.3 V	0		0.32	V
	VIL3	P20 to P23		0		0.3V _{DD}	٧
	V _{IL4}	P60, P61		0		0.3V _{DD}	٧
	V _{IL5}	P121, P122, P125 ^{Note 1} , P137, I	EXCLK, RESET	0		0.2V _{DD}	٧
Output voltage, high	V _{OH1}	20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14,	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	V _{DD} -0.7			V
		P40 to P42 30-pin products:	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -2.0 \text{ mA}$	V _{DD} -0.6			V
		P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -1.5 \text{ mA}$	V _{DD} -0.5			V
	V _{OH2}	P20 to P23	Iон2 = -100 µА	V _{DD} -0.5			V

Notes 1. 20, 24-pin products only.

2. 24-pin products only.

Caution The maximum value of V_{IH} of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is V_{DD} even in N-ch open-drain mode. High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(1) 20-, 24-pin products

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit	
Supply	IDD2 Note 2	HALT	HS (High-speed	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		440	2230	μA	
current ^{Note 1}		mode	main) mode ^{Note 6}		V _{DD} = 3.0 V		440	2230		
				fıн = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		400	1650	μA	
				V _{DD} = 3.0 V		400	1650			
					$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		280	1900	μΑ
				V _{DD} = 5.0 V	Resonator connection		450	2000		
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		280	1900	μΑ	
		V _{DD} = 3.0 V	Resonator connection		450	2000				
			$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$ $V_{DD} = 5.0 \text{ V}$	fmx = 10 MHz ^{Note 3} ,	Square wave input		190	1010	μА	
				Resonator connection		260	1090			
				fmx = 10 MHz ^{Note 3} ,	Square wave input		190	1010	μΑ	
				V _{DD} = 3.0 V	Resonator connection		260	1090		
	IDD3 Note 5	STOP	T _A = -40°C				0.19	0.50	μΑ	
		mode	T _A = +25°C				0.24	0.50		
			T _A = +50°C	T _A = +50°C			0.32	0.80		
	$T_A = +70^{\circ}C$ $T_A = +85^{\circ}C$	T _A = +70°C				0.48	1.20			
		T _A = +85°C				0.74	2.20			
			T _A = +105°C				1.50	10.20		

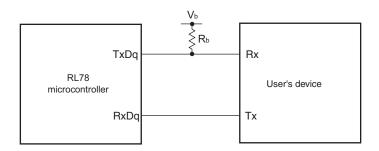
- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator clock is stopped.
 - 4. When high-speed system clock is stopped.
 - 5. Not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: $V_{DD} = 2.7 \text{ V to } 5.5 \text{ V}$ @1 MHz to 24 MHz $V_{DD} = 2.4 \text{ V to } 5.5 \text{ V}$ @1 MHz to 16 MHz

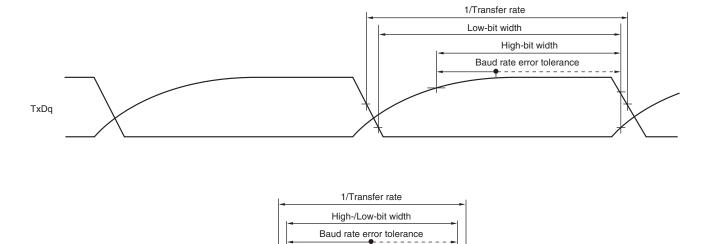
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - 3. Except temperature condition of the TYP. value is $T_A = 25$ °C, other than STOP mode

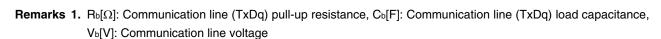
RxDq

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **2.** q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
 - m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))
- **4.** UART0 of the 20- and 24-pin products supports communication at different potential only when the peripheral I/O redirection function is not used.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

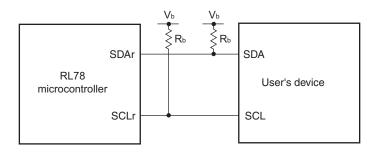
(Ta = -40 to +105°C, 2.4 V \leq VDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions	HS (high-speed	d main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$4.0 \ V \leq V_{DD} \leq 5.5 \ V,$ $2.7 \ V \leq V_b \leq 4.0 \ V,$	600		ns
			$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$			
			$2.7 \ V \le V_{DD} < 4.0 \ V,$ $2.3 \ V \le V_b \le 2.7 \ V,$	1000		ns
			$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
			$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$	2300		ns
			$1.6 \ V \le V_b \le 2.0 \ V,$			
			$C_b=30~pF,~R_b=5.5~k\Omega$			
SCKp high-level width	t _{KH1}	$4.0 \text{ V} \leq \text{V}_{DD} \leq 3$	$4.0~V \le V_{DD} \le 5.5~V,~2.7~V \le V_b \le 4.0~V,$			ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$				
		2.7 V ≤ V _{DD} < 4	$4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	tксү1/2 -340		ns
		C _b = 30 pF, R _b	$_{0}$ = 2.7 k Ω			
		2.4 V ≤ V _{DD} < 3	$3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$	tkcy1/2 -916		ns
		C _b = 30 pF, R _b	$_{0}$ = 5.5 k Ω			
SCKp low-level width	t _{KL1}	$4.0 \text{ V} \leq \text{V}_{DD} \leq 3$	$5.5~V,~2.7~V \leq V_b \leq 4.0~V,$	tксү1/2 -24		ns
		Cb = 30 pF, Rb	$_{0}$ = 1.4 k Ω			
		2.7 V ≤ V _{DD} < 4	$4.0 \ V, \ 2.3 \ V \le V_b \le 2.7 \ V,$	tксү1/2 -36		ns
		C _b = 30 pF, R _b	$C_b = 30$ pF, $R_b = 2.7$ k Ω			
		2.4 V ≤ V _{DD} < 3	$3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V},$	tkcy1/2 -100		ns
		C _b = 30 pF, R _b	$_{0}$ = 5.5 k Ω			

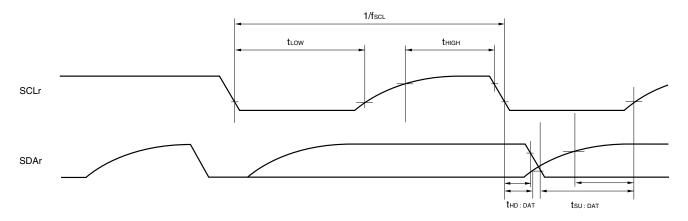
- Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For VH and VL, see the DC characteristics with TTL input buffer selected.
 - 2. CSI01 and CSI11 cannot communicate at different potential.
- **Remarks 1.** R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 20)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remarks 1.** Rb $[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, Cb [F]: Communication line (SDAr, SCLr) load capacitance, Vb [V]: Communication line voltage
 - **2.** r: IIC Number (r = 00, 20)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number (m = 0,1), n: Channel number (n = 0)

3.5.2 Serial interface IICA

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS	(high-spee	ed main) m	node	Unit
			Standa	rd Mode	Fast		
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fclk≥ 3.5 MHz			0	400	kHz
		Normal mode: fclk≥ 1 MHz	0	100			kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μS
Hold time ^{Note 1}	thd:STA		4.0		0.6		μS
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μS
Hold time when SCLA0 = "H"	thigh		4.0		0.6		μS
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	3.45	0	0.9	μS
Setup time of stop condition	tsu:sto		4.0		0.6		μS
Bus-free time	t BUF		4.7		1.3		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

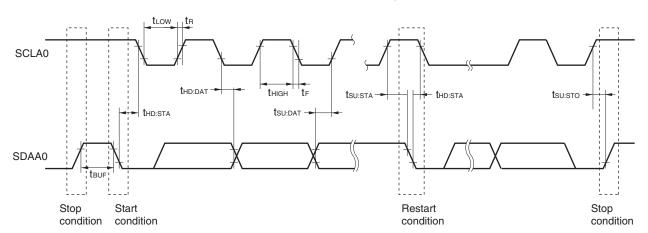
2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution Only in the 30-pin products, the values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VoH1, VoL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Normal mode: $C_b = 400 \text{ pF}, \text{ Rb} = 2.7 \text{ k}\Omega$ Fast mode: $C_b = 320 \text{ pF}, \text{ Rb} = 1.1 \text{ k}\Omega$

IICA serial transfer timing



<R>

3.6.2 Temperature sensor/internal reference voltage characteristics

(T_A = -40 to +105°C, 2.4 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode

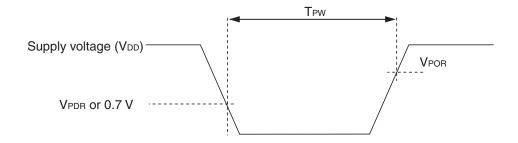
1 11 11 1	,	· · · · · · · · · · · · · · · · · · ·				
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.50	V
Temperature coefficient	FVTMPS	Temperature sensor output voltage that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

3.6.3 POR circuit characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.45	1.51	1.57	V
	V _{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width Note	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{PDR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



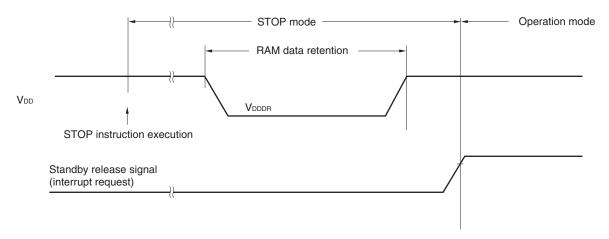


<R> 3.7 RAM Data Retention Characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V _{DDDR}		1.44 Note		5.5	V

<R> Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.8 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk		1		24	MHz
Code flash memory rewritable times	Cerwr	Retained for 20 years TA = 85°C Notes 4	1,000			Times
Data flash memory rewritable times		Retained for 1 year TA = 25°C Notes 4		1,000,000		
		Retained for 5 years TA = 85°C Notes 4	100,000			
		Retained for 20 years TA = 85°C Notes 4	10,000			

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 - 2. When using flash memory programmer and Renesas Electronics self programming library
 - **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
 - 4. This temperature is the average value at which data are retained.





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